

FGP90N30

300V, 90A PDP IGBT

Features

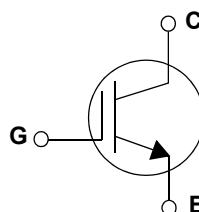
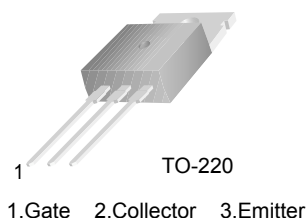
- High Current Capability
- Low saturation voltage : $V_{CE(sat)} = 1.1 \text{ V @ } I_C = 20\text{A}$
- High input impedance
- Fast switching

Application

. PDP System

General Description

Employing Unified IGBT Technology, Fairchild's PDP IGBTs provides low conduction and switching loss. The PWD series offers the optimum solution for PDP applications where low - conduction loss is essential.



Absolute Maximum Ratings

Symbol	Description	FGP90N30	Units
V_{CES}	Collector-Emitter Voltage	300	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	90	A
$I_{C_pulse (1)}$	Pulse Collector Current @ $T_C = 25^\circ\text{C}$	130	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	192	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	77	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.65	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

Notes

(1) Repetitive test , pulse width=100usec , Duty=0.5

Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGP90N30	FGP90N30TU	TO-220	Rail / Tube	50ea	-

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	300	--	--	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	--	0.6	--	V/ $^\circ\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	100	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 250	nA

On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\mu A, V_{CE} = V_{GE}$	2.5	4.0	5.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 20A, V_{GE} = 15V$	--	1.1	1.4	V
		$I_C = 90A, V_{GE} = 15V$ $T_C = 25^\circ\text{C}$	--	1.9	--	V
		$I_C = 90A, V_{GE} = 15V$ $T_C = 125^\circ\text{C}$	--	2.0	--	V

Dynamic Characteristics

C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1\text{MHz}$	--	1700	--	pF
C_{oes}	Output Capacitance		--	290	--	pF
C_{res}	Reverse Transfer Capacitance		--	80	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 200V, I_C = 20A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Resistive Load, $T_C = 25^\circ\text{C}$	--	30	--	ns
t_r	Rise Time		--	150	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	--	ns
t_f	Fall Time		--	140	350	ns
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 200V, I_C = 20A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Resistive Load, $T_C = 125^\circ\text{C}$	--	30	--	ns
t_r	Rise Time		--	150	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	--	ns
t_f	Fall Time		--	330	--	ns
Q_g	Total Gate Charge	$V_{CE} = 200V, I_C = 20A,$ $V_{GE} = 15V$	--	87	130	nC
Q_{ge}	Gate-Emitter Charge		--	12	18	nC
Q_{gc}	Gate-Collector Charge		--	38	57	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

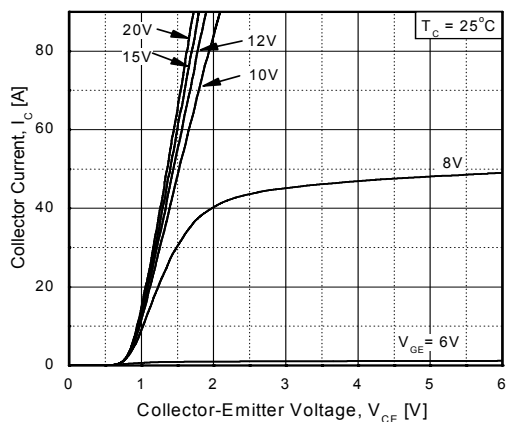


Figure 2. Typical Output Characteristics

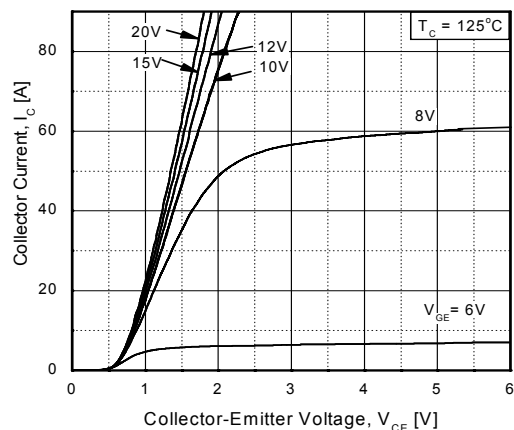


Figure 3 Typical Saturation Voltage Characteristics

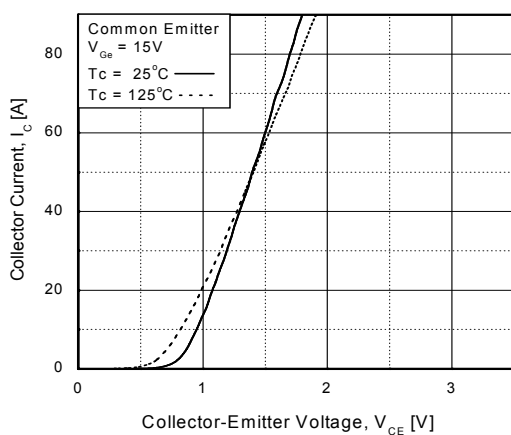


Figure 4. Transfer Characteristics

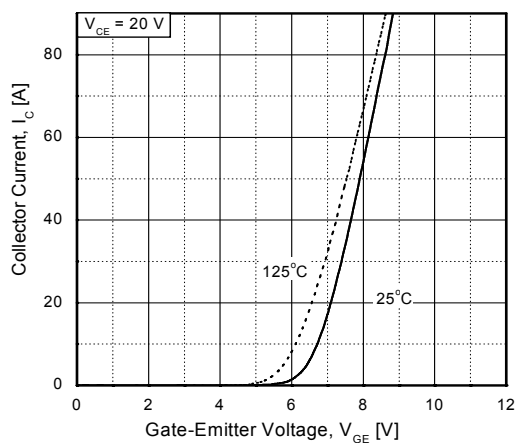


Figure 5. Saturation Voltage vs Case Temperature at Variant Current Level

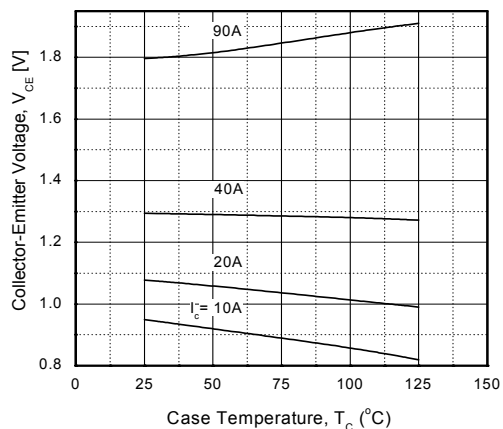


Figure 6. Saturation Voltage vs. Vge

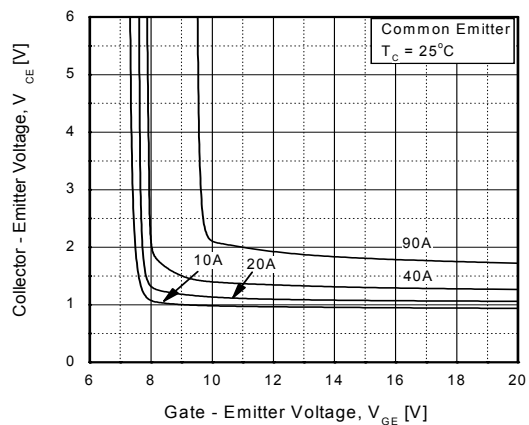


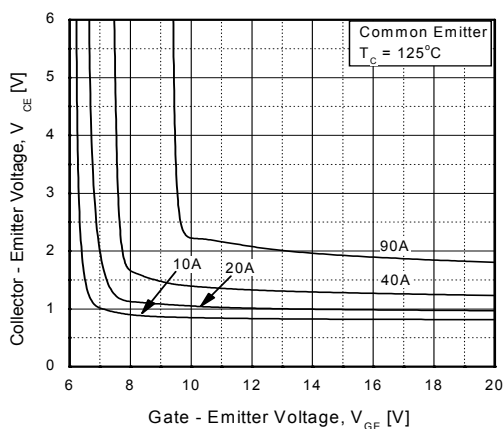
Figure 7. Saturation Voltage vs. V_{GE} 

Figure 8. Capacitance Characteristics

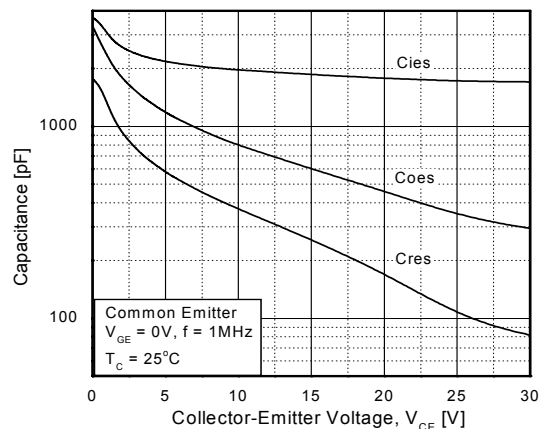


Figure 9. Gate Charge

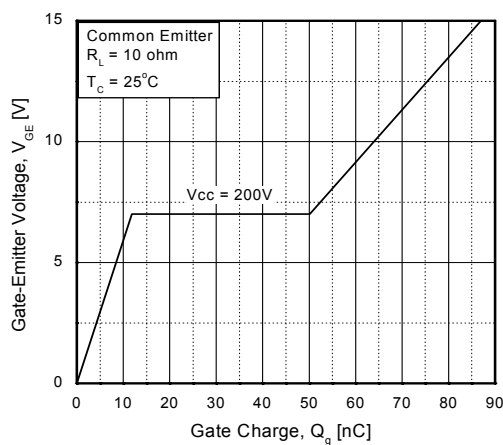


Figure 10. SOA Characteristics

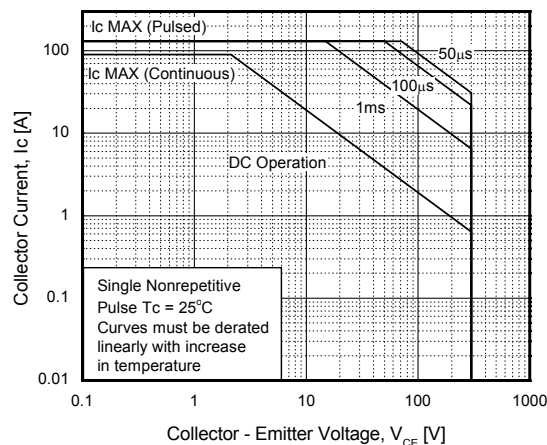


Figure 11. Turn-On Characteristics vs. Gate Resistance

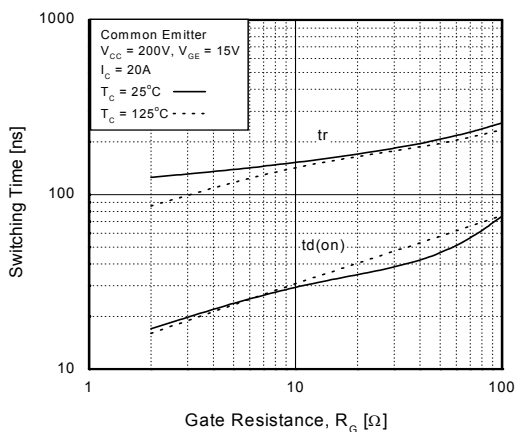


Figure 12. Turn-Off Characteristics vs. Gate Resistance

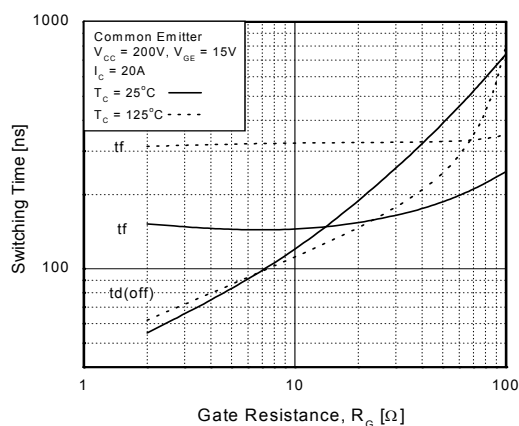


Figure 13 Turn-On Characteristics vs. Collector Current

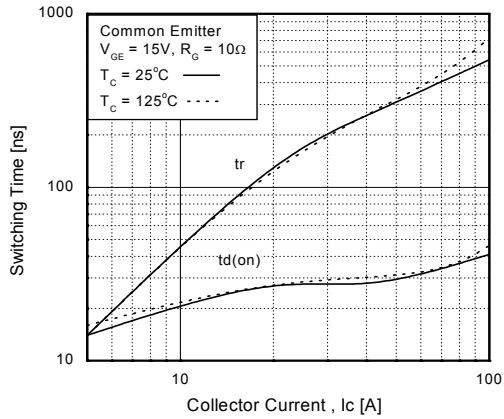


Figure 14. Turn-Off Characteristics vs. Collector Current

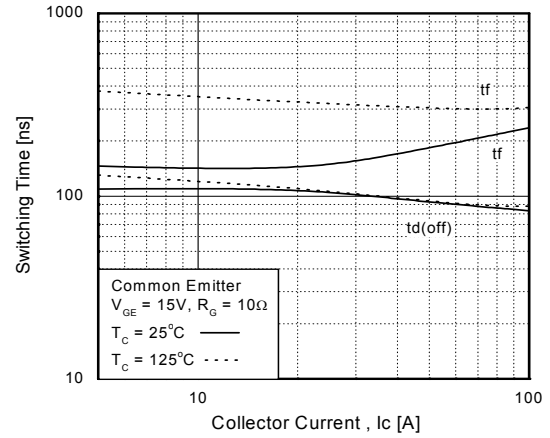


Figure 15. Switching Loss vs. Gate Resistance

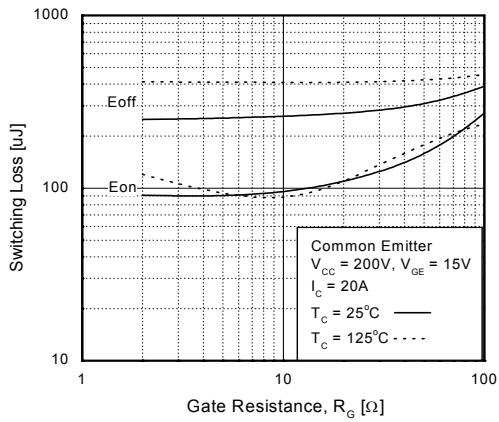


Figure 16. Switching Loss vs. Collector Current

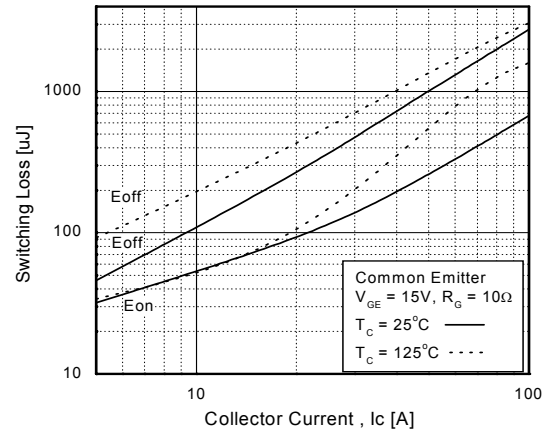
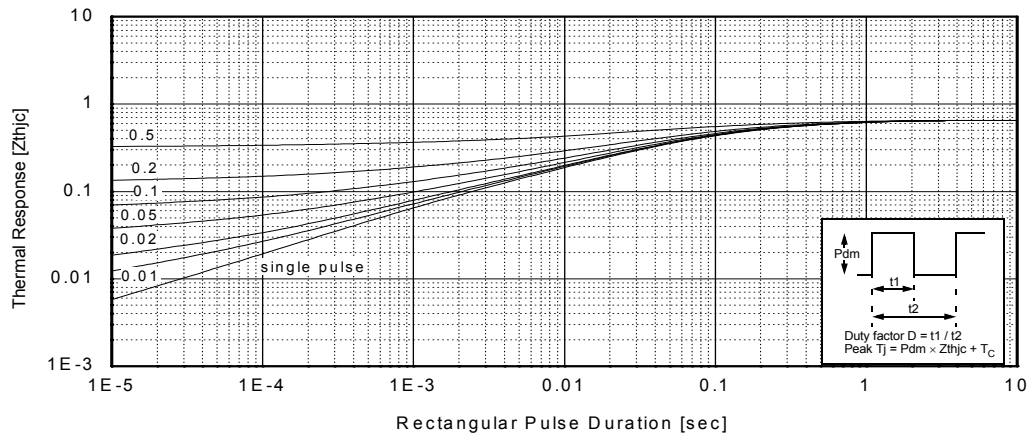
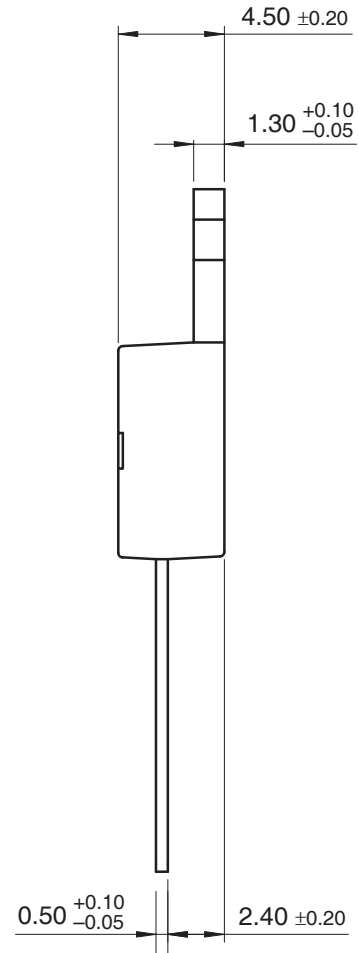
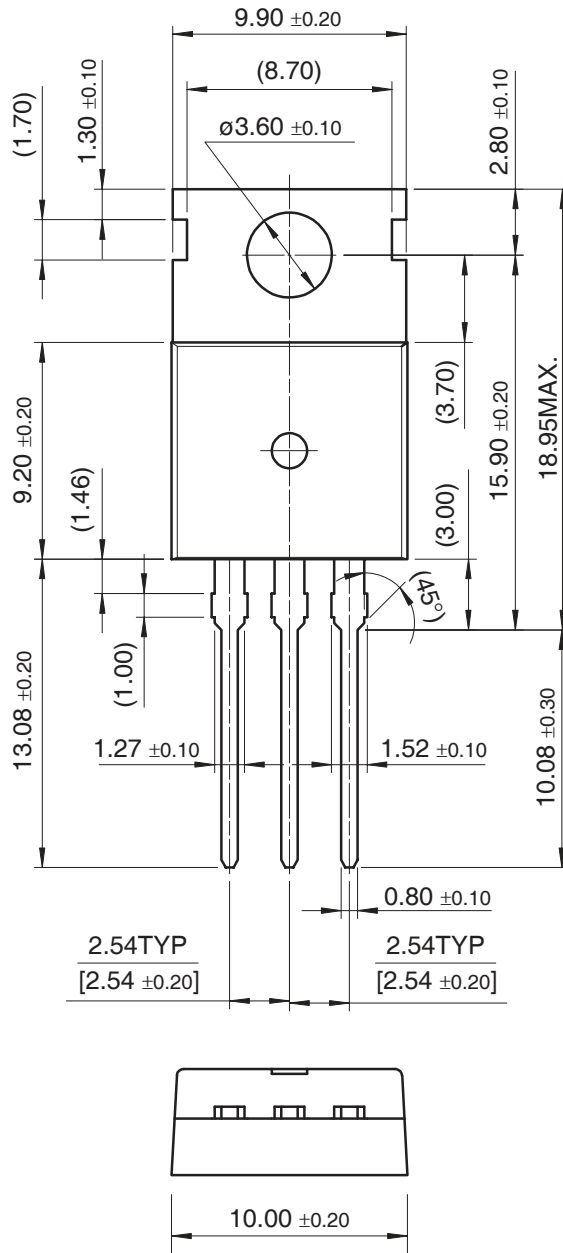


Figure 17. Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-220



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Rev. 117

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FGP90N30

300V, 90A PDP IGBT

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General description

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- Fast switching

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Applications

- PDP System

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Product status/pricing/packageing

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Product	Product status	Pb-free Status	Pricing*	Package type	Leads	Packing method	Package Marking Convention**

FGP90N30TU	Full Production		\$2.52	TO-220	3	RAIL	Line 1: \$Y (Fairchild logo) &Z (Asm. Plant Code) &E&3 (3-Digit Date Code) Line 2: FGP Line 3: 90N30
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* Fairchild 1,000 piece Budgetary Pricing

** A sample button will appear if the part is available through Fairchild's on-line samples program. If there is no sample button, please contact a [Fairchild distributor](#) to obtain samples



Indicates product with Pb-free second-level interconnect. For more information [click here](#).

Package marking information for product FGP90N30 is available. [Click here for more information](#).

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Qualification Support

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Product
FGP90N30TU

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